Sunday, September 1

10:25-16:00 Short Course 1(Room A (407)), Short Course 2 (Room B＋C (408＋409))
16:30-18:00 Special Talk Session (Grand Hall Foyer)
18:00-19:30 Welcome Reception (Grand Hall Foyer)

Monday, September 2

9:00-12:50 Opening and Plenary Sessions (Grand Hall)

Lunch

Room A (407)	Room B (408)	Room C (409)	Room D (Medium Hall)	Room E (401)	Room F (402)	Room G (403)	Room H (Small Hall)	Room J (Main Studio)	Room K (404)	Room M (Special Conference Room)	Room N (Studio 1)
14:30-16:00 [A-1] Advanced CMOS: Process Technology	**14:30-15:45** [B-1] Ferroelectric Memory Materials	**14:30-15:45** [C-1] Advanced Metallization I	**14:30-16:00** [D-1] Ga2O3 Power Devices		**14:30-15:45** [F-1] Thermoelectric materials and devices I		**14:30-15:30** [H-1] Device-I	**14:30-15:30** [J-1] Qubit I	**14:15-16:00** [K-1] Oxide-TFTs I	**14:30-16:00** [M-1] Oxide Materials	**14:30-15:45** [N-1] Sensor Circuits and Systems
Coffee Break											
16:15-17:30 [A-2] Innovative devices and Sensing technology	**16:15-17:30** [B-2] In-Memory and Unconventional Computing I	**16:15-16:45** [C-2] MEMS and Advanced Metallization I	**16:30-17:30** [D-2] Diamond Devices	**16:15-17:30** [E-2] Integrated Light Source and Related Technology	**16:15-17:30** [F-2] Thermoelectric materials and devices II		**16:15-17:30** [H-2] Characterization-I	**16:15-17:15** [J-2] Qubit II	**16:15-17:30** [K-2] Oxide-TFTs II	**16:15-17:30** [M-2] Characterization and Device Applications	

18:30-21:00 Banquet (Himeji Castle)

Tuesday, September 3

Room A (407)	Room B (408)	Room C (409)	Room D (Medium Hall)	Room E (401)	Room F (402)	Room G (403)	Room H (Small Hall)	Room J (Main Studio)	Room K (404)	Room M (Special Conference Room)	Room N (Studio 1)
	9:00-10:15 [B-3] Ferroelectric Devices		**9:00-10:00** [D-3] Si-related Devices	**9:00-10:15** [E-3] Si Photonics		**9:00-9:45** [G-3] Organic / Molecular / Bio-electronics Late News Session	**9:00-10:00** [H-3] Growth	**9:00-10:00** [J-3] Novel Quantum Devices			
Coffee Break											
10:45-12:15 [A-4] Advanced CMOS: Device Technology	**10:45-12:15** [B-4] Ferroelectric Memory Devices	**10:45-12:00** [C-4] Advanced integration	**10:45-12:00** [D-4] High-speed Devices	**10:45-12:00** [E-4] UV and Visible Light Technology	**10:45-11:45** [F-4] Energy harvesting and solar cells	**10:30-12:00** [G-4] Highly Sensitive Devices for Chem/Bio Detection	**10:45-11:45** [H-4] Device-II	**10:45-12:00** [J-4] Spintronics		**10:45-12:00** [M-4] Wide Bandgap Materials	**10:45-12:15** [N-4] Emerging Memory Devices, and DRAM
Lunch											
13:30-14:02 Short Oral Presentation	**13:30-14:28** Short Oral Presentation	**13:30-13:46** Short Oral Presentation	**13:30-14:10** Short Oral Presentation	**13:30-13:54** Short Oral Presentation	**13:30-13:46** Short Oral Presentation	**13:30-13:48** Short Oral Presentation	**13:30-13:52** Short Oral Presentation	**13:30-13:52** Short Oral Presentation	**13:30-14:00** Short Oral Presentation	**13:30-13:54** Short Oral Presentation	**13:30-13:38** Short Oral Presentation
Coffee Break											

15:00-17:00 Poster Session (Exibition Hall A)

Wednesday, September 4

Room A (407)	Room B (408)	Room C (409)	Room D (Medium Hall)	Room E (401)	Room F (402)	Room G (403)	Room H (Small Hall)	Room J (Main Studio)	Room K (404)	Room M (Special Conference Room)	Room N (Studio 1)
9:00-10:00 [A-5] Ferroelectric Devices	**9:00-10:30** [B-5] In-Memory and Unconventional Computing II	**9:00-10:00** [C-5] Advanced Metallization II	**9:00-10:30** [D-5] SiC MOS Interfaces			**9:00-10:15** [G-5] Advanced Devices for Medical Applications	**9:00-10:15** [H-5] Characterization-II	**9:00-10:00** [J-5] Novel devices for neuromorphic applications		**9:00-10:15** [M-5] Advanced Materials and Thin Films	
Coffee Break											
10:45-12:15 [A-6] Modeling, Simulation and Characterization	**10:45-12:15** [B-6] 3D NAND Flash Memory	**10:45-12:00** [C-6] MEMS and Advanced Metallization II	**11:00-12:15** [D-6] SiC Power Devices		**10:30-12:00** [F-6] Solar cells	**10:45-12:15** [G-6] Advanced Lab-on-Chip Devices and Organic/Inorganic Hybrid Electronics	**10:45-11:45** [H-6] Device-III	**10:45-11:30** [J-6] Novel advanced materials	**10:30-12:00** [K-6] Group-IV Thin-film Technologies	**10:45-12:00** [M-6] Low Dimensional Materials	**10:45-11:45** [N-6] Compute-in-Memory
Lunch											
13:30-14:45 [A-7] Advanced CMOS: CFET	**13:30-14:45** [B-7] ReRAM, PCRAM, and FeRAM		**13:30-14:30** [D-7] GaN Power Devices	**13:30-14:30** [E-7] Metamaterials and Metasurfaces		**13:30-14:45** [G-7] Organic Electronics I	**13:30-14:30** [H-7] Device-IV		**13:30-15:00** [K-7] Ferroelectric Materials and Late News	**13:30-14:45** [M-7] Group IV Materials	**13:30-14:30** [N-7] Advanced Circuits and Devices
Coffee Break											
	15:15-16:30 [B-8] Ferroelectric FET		**15:15-16:15** [D-8] Processes and Characterization	**15:15-16:15** [E-8] Sensors and Detectors		**15:15-16:30** [G-8] Organic Electronics II					

Area Scope
- Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology
- Area 2: Advanced and Emerging Memories / New Applications
- Area 3: Heterogeneous and 3D Integration / Interconnect / MEMS
- Area 4: Power / High–speed Devices and Materials
- Area 5: Photonics: Devices / Integration / Related Technology
- Area 6: Energy Harvesting and Converting Devices and Materials

Area Scope
- Area 7: Organic / Molecular / Bio–electronics
- Area 8: Low Dimensional Devices and Materials
- Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
- Area 10: Thin Film Electronics: Oxide / Non–single Crystalline / Novel Process
- Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
- Area12: Advanced Circuits / Systems Interacting with Innovative Devices and Materials